



BC847BV

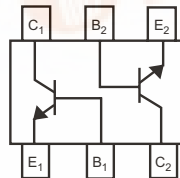
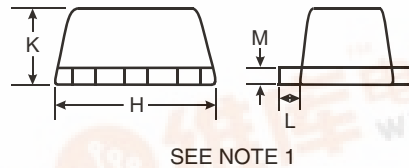
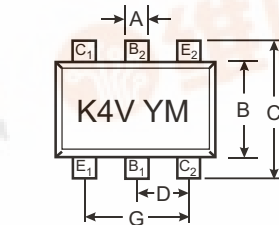
NPN DUAL SMALL SIGNAL SURFACE MOUNT TRANSISTOR

Features

- Epitaxial Die Construction
- Complementary PNP Type Available (BC857BV)
- Ultra-Small Surface Mount Package
- **Lead Free By Design/RoHS Compliant (Note 3)**

Mechanical Data

- Case: SOT-563
- Case Material: Molded Plastic. UL Flammability Classification Rating 94V-0
- Moisture sensitivity: Level 1 per J-STD-020C
- Terminal Connections: See Diagram
- Terminals: Finish - Matte Tin annealed over Alloy 42 leadframe. Solderable per MIL-STD-202, Method 208
- Marking (See Page 2): K4V
- Ordering & Date Code Information: See Page 2
- Weight: 0.002 grams (approx.)



SOT-563			
Dim	Min	Max	Typ
A	0.15	0.30	0.25
B	1.10	1.25	1.20
C	1.55	1.70	1.60
D	0.50		
G	0.90	1.10	1.00
H	1.50	1.70	1.60
K	0.56	0.60	0.60
L	0.10	0.30	0.20
M	0.10	0.18	0.11
All Dimensions in mm			

Maximum Ratings @ T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CB0}	50	V
Collector-Emitter Voltage	V _{CEO}	45	V
Emitter-Base Voltage	V _{EB0}	6.0	V
Collector Current	I _C	100	mA
Power Dissipation (Note 2)	P _d	150	mW
Thermal Resistance, Junction to Ambient (Note 2)	R _{θJA}	833	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

- Notes:
1. Package is non-polarized. Parts may be on reel in orientation illustrated, 180° rotated, or mixed (both ways).
 2. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch; pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at <http://www.diodes.com/datasheets/ap02001.pdf>.
 3. No purposefully added lead.

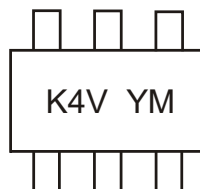
Electrical Characteristics @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
Collector-Base Breakdown Voltage (Note 4)	$V_{(BR)CBO}$	50	—	—	V	$I_C = 10\mu\text{A}$, $I_B = 0$
Collector-Emitter Breakdown Voltage (Note 4)	$V_{(BR)CEO}$	45	—	—	V	$I_C = 10\text{mA}$, $I_B = 0$
Emitter-Base Breakdown Voltage (Note 4)	$V_{(BR)EBO}$	6	—	—	V	$I_E = 1\mu\text{A}$, $I_C = 0$
DC Current Gain (Note 4)	h_{FE}	200	290	450	—	$V_{CE} = 5.0\text{V}$, $I_C = 2.0\text{mA}$
Collector-Emitter Saturation Voltage (Note 4)	$V_{CE(SAT)}$	—	—	100 300	mV	$I_C = 10\text{mA}$, $I_B = 0.5\text{mA}$ $I_C = 100\text{mA}$, $I_B = 5.0\text{mA}$
Base-Emitter Saturation Voltage (Note 4)	$V_{BE(SAT)}$	—	700 900	—	mV	$I_C = 10\text{mA}$, $I_B = 0.5\text{mA}$ $I_C = 100\text{mA}$, $I_B = 5.0\text{mA}$
Base-Emitter Voltage (Note 4)	V_{BE}	580 —	660 —	700 770	mV	$V_{CE} = 5.0\text{V}$, $I_C = 2.0\text{mA}$ $V_{CE} = 5.0\text{V}$, $I_C = 10\text{mA}$
Collector-Emitter Cutoff Current (Note 4)	I_{CBO} I_{CBO}	—	—	15 5.0	nA μA	$V_{CB} = 30\text{V}$ $V_{CB} = 30\text{V}$, $T_A = 150^\circ\text{C}$
Gain Bandwidth Product	f_T	100	—	—	MHz	$V_{CE} = 5.0\text{V}$, $I_C = 10\text{mA}$, $f = 100\text{MHz}$
Output Capacitance	C_{OBO}	—	—	4.5	pF	$V_{CB} = 10\text{V}$, $f = 1.0\text{MHz}$
Noise Figure	NF	—	—	10	dB	$V_{CE} = 5\text{V}$, $R_S = 2.0\text{k}\Omega$, $f = 1.0\text{kHz}$, BW = 200Hz

Ordering Information (Note 5)

Device	Packaging	Shipping
BC847BV-7	SOT-563	3000/Tape & Reel

- Notes: 4. Short duration pulse test used to minimize self-heating effect.
 5. For Packaging Details, go to our website at <http://www.diodes.com/datasheets/ap02007.pdf>.

Marking Information


K4V = Product Type Marking Code
 YM = Date Code Marking
 Y = Year (ex: P = 2003)
 M = Month (ex: 9 = September)

Date Code Key

Year	2003	2004	2005	2006	2007	2008	2009
Code	P	R	S	T	U	V	W

Month	Jan	Feb	March	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

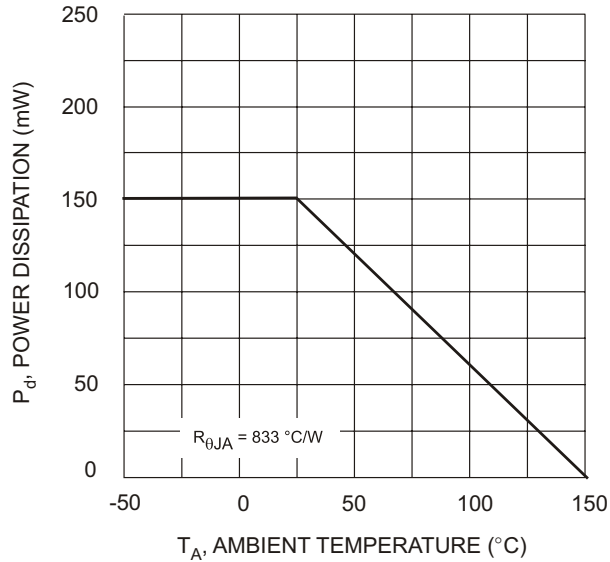


Fig. 1, Derating Curve - Total

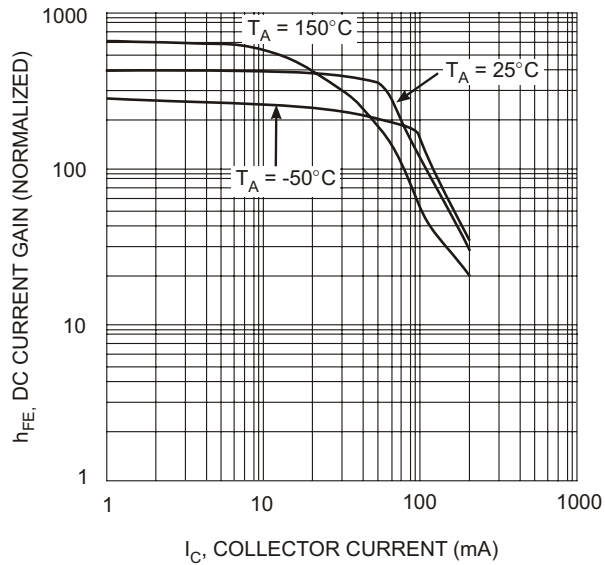


Fig. 3, DC Current Gain vs Collector Current

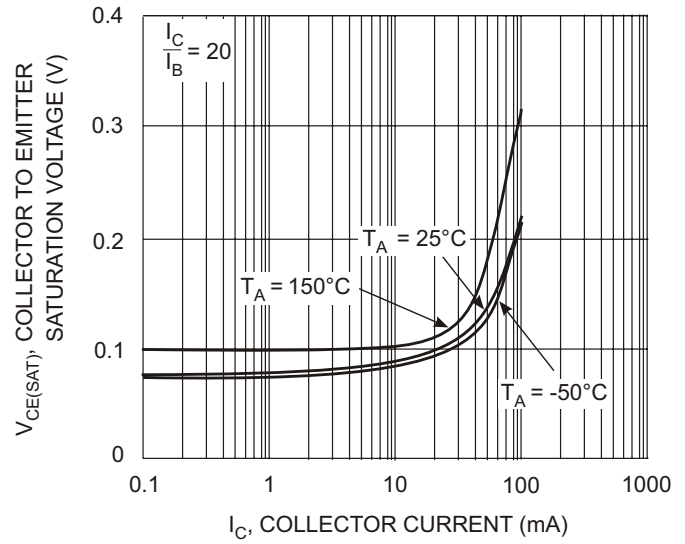


Fig. 2, Collector Emitter Saturation Voltage vs. Collector Current

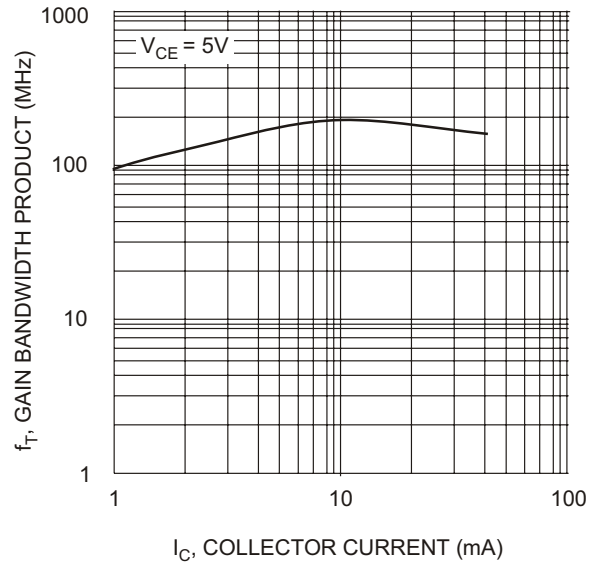


Fig. 4, Gain Bandwidth Product vs Collector Current